

Table of Contents

Preface	iii
Contents	v
Facts about ECS	x

Applications of Bonded SOI Substrates

High Performance SOI Device Options S.-F. Huang (Invited)	1
Applications of Bonding SOI Technology to High Performance LSI Circuits M. Yoshimi, F. Letertre, I. Cayrefourcq, and C. Mazuré (Invited)	9
Device Applications Using Bonded SOI Wafers S. Fujino, H. Himi, T. Fukada, and H. Yamaguchi (Invited)	20

Advanced Bonding and Transfer Techniques

Surface Plasma Activation Before Direct Wafer Bonding: A Short Review and Recent Results H. Moriceau, F. Rieutord, C. Morales, S. Sartori, and A.M. Charvet (Invited)	34
Capabilities of an Ambient Pressure Plasma for Activation in LT Wafer Bonding Processes M. Gabriel, V. Cetin, S. Hansen, M. Reiche, I. Radu, and M. Eichler	50
Plasma Bonding Replacement Methods for Traditional Bond Technologies S. Farrens, V. Dragoi, and R. Pelzer, M. Wimplinger, and P. Lindner	58
Direct Wafer Bonding and Thinning Down: A Generic Technology to Perform New Structures B. Aspar, C. Lagahe-Blanchard, and H. Moriceau (Invited)	64
200 mm Germanium-on-Insulator (GeOI) Structures Realized from Epitaxial Wafers using the Smart Cut™ Technology C. Deguet, J. Dechamp, C. Morales, A.M. Charvet, L. Clavelier, V. Loup, J.M. Hartmann, N. Kernevez, Y. Campidelli, F. Allibert, C. Richtarce, T. Akatsu, and F. Letertre	78
Wafer Bonding and Layer Transfer Approach for Strained Silicon-on-Insulator (SSOI) Fabrication R. Singh, I. Radu, M. Reiche, U. Gösele, S.H. Christiansen, and D. Webb	89
Layer Transfer and Characterization of SOI and GeOI Substrates Z.X. Liu, V. Loryuenyoung, N.W. Cheung, B. Schmidt, P. Chen, and S.S. Lau	96

Alternative and Engineered Substrate Bonding

- Recent Progress in Engineered Substrates for GaN Microelectronic Applications 106
B. Faure, A. Boussagol, H. Larheche, S. Bressot, D. Da Cruz, P. Bove,
and F. Letertre (Invited)
- Transfer of Two-Inch GaN Film by the Smart Cut™ Technology 119
A. Tauzin, T. Akatsu, M. Rabarot, J. Dechamp, M. Zussy, H. Moriceau,
J.F. Michaud, A.M. Charvet, L. Di Cioccio, F. Fournel, J. Garrione, F. Letertre,
B. Faure, and N. Kernevez
- Low Temperature Integration of CdZnTe(211)B/Si(100) by Wafer Bonding 128
J. Huang, D.K. Cha, A. Kaleczyc, J.H. Dinan, R.W. Carpenter, and M.J. Kim
- Implantation Temperature Effect on the Defect Profile in Hydrogen
Implanted InP 134
S. Hayashi, R. Sandhu, D. Bruno, M. Wojtowicz, and M.S. Goorsky
- GaN-Based Light-Emitting Diodes for Vertical Current Injection by
Laser Lift-off and Wafer Bonding Techniques 140
R.-H. Horng, K.-F. Pan, C.-E. Lee, S.-H. Hung, W.-Y. Lin, Y.-Y. Su,
C.-C. Yang, and D.-S. Wu
- AlGaIn/GaN Heterostructure Field Effect Transistors Fabricated on 100mm
Si/Poly SiC Composite Substrates 151
J. C. Roberts, P. Rajagopal, J.W. Cook, Jr., R.J. Therrien, E.L. Piner,
K. J. Linthicum, K.D. Hobart, M. Twigg, J. Mittereder, S. Binari, and F.J. Kub

Wafer Bonding for MEMS Applications

- Wafer Bonding for MEMS 157
P. Enoksson, C. Rusu, A. Sanz-Velasco, M. Bring, A. Nafari,
and S. Bengtsson (Invited)
- Wafer Scale Packaging of MEMS by Using Plasma Activated Wafer Bonding 173
T. Suni, K. Henttinen, A Lipsanen, J. Dekker, H. Luoto, and M. Kulawski
- Wafer Bonding for Optical MEMS 184
T. Bakke, B. Völker, H. Schenk, I. Radu, and M. Reiche
- Direct Bonding of Thick Film Polysilicon to Glass Substrates 194
H. Luoto, T. Suni, K. Henttinen, and M. Kulawski
- Low- and High-Temperature Silicon Wafer Direct Bonding for Micromachined
Absolute Pressure Sensors 205
R. Knechtel, G. Dahlmann, and U. Schwarz

SOI Wafers with Buried Cavities 216
T. Suni, K. Henttinen, J. Dekker, H. Luoto, M. Kulawski, J. Mäkinen,
and R. Mutikainen

Si-Based Condenser Microphone by Wafer Bonding Technique 226
R.-H. Horng, Z.-T. Yuan, K.-Y. Hu, and C.-C. Chang

In-Line Critical Leak Rate Testing of Vacuum-Sealed and Backfilled
Resonating MEMS Devices 233
W. Reinert, D. Kähler, M. Oldsen, and P. Merz

Mechanical Characterization of Wafer Bonded Substrates

Mechanical Aspects of Wafer Bonding 241
K.T. Turner and S.M. Spearing (Invited)

Mechanical Reliability of Directly Bonded Silicon MEMS Components 253
J. Bagdahn, M. Wiemer, and M. Petzold (Invited)

Influence of a Ductile Interlayer on the Toughness of Hydrophilic
Wafer Bonding 264
Y. Bertholet, J.P. Raskin, and T. Pardoen

Effect of Wafer-Scale Shape Variations and Mounting in Wafer Bonding 270
K.T. Turner, S.M. Spearing, P. Hester, J. Sinha, and W.A. Baylies

Low Temperature Wafer Bonding for SOI and MEMS

Recent Results on Advanced Molecular Wafer Bonding Technology for 3D
Integration on Silicon 280
L. di Cioccio, B. Biasse, M. Kostrzewa, M. Zussy, J. Dechamp, B. Charlet,
M. Vinet, J.M. Fedeli, T. Poiroux, C. Lagahe-Blanchard, B. Aspar,
P. Regreny, and N. Kernevez

Surface Energy of Fusion Bonded Silicon Nitride to Silicon 288
K. Midtbø, K. Schjølberg-Henriksen, M.M.V Taklo, and A. Rønnekleiv

Low-Temperature Wafer Bonding via DBD Surface Activation 295
I. Radu, M. Reiche, M. Zoberbier, M. Gabriel, and U. Gösele

Fabrication of SOI Substrates with Buried Silicide Layers for BiCMOS
Applications 303
M. Wiemer, S. Zimmermann, Q.T. Zhao, B. Trui, C. Kaufmann, S. Mantl,
V. Dudek, and T. Gessner

Low-Temperature Silicon Wafer Bonding with Titanium 311
J. Yu, Y.M. Wang, J.-Q. Lu, and R.J. Gutmann

Activation Process and Bonding Mechanism of Si/LiNbO ₃ and LiNbO ₃ / LiNbO ₃ at Room Temperature M.R. Howlader, T. Suga, and M. J. Kim	319
Mechanisms of Low-Temperature Wafer Bonding M. Reiche, I. Radu, M. Gabriel, M. Zoberbier, S. Hansen, and M. Eichler	326
X-Ray Characterization of Bonding Interfaces F. Rieutord, H. Moriceau, B. Bataillou, C. Morales, and J. Eymery	338
Atomically Flat Surface of Hydrogen Transferred Si Film with Boron Delta Doped Layer V.P. Popov, L.V. Safronov, A.I. Nikiforov, and R. Sholz	346
Electrical Properties of Low-Temperature Bonded Unipolar Si/Si Junctions B. Raecissi Nafchi, P. Amirfeiz, and O. Engström	355
Direct Wafer Fusion of GaAs Thin Film on InP by Chemical and Plasma Activation J. Arokiaraj, S. Vicknesh, S. Tripathy, and A. Ramam	367
UV Activation Treatment for Hydrophobic Wafer Bonding H. Dang, S.L. Holl, C.A. Colinge, K.D. Hobart, and F.J. Kub	376
Oxide Free Transfer of Silicon Layers in UHV A. M. Fecioru, S. Senz, and U. M. Gösele	385
Room Temperature UHV Bonding of Si to GaAs A. M. Fecioru, S. Senz, and U. M. Gösele	392
Silicon Wafer Bonding Using Deposited and Thermal Oxides: A Comparative Study I. Radu, R. Singh, M. Reiche, U. Gösele, B. Kuck, T. Grabolla, B. Tillack, and S. Christiansen	400
UHV- Direct Bonding of Semiconductor Wafers at Room Temperature Using Hydrogen Ion Beam Surfaces Cleaning N. Razek, A. Schindler, D. Hirsch, G. Wagner, V. Gottschalch, and B. Rauschenbach	406
Thermal-Microwave Hybrid SOI Materials Technology J.T. Cheng, C.-H. Huang, Y.-K. Hsu, C.-L. Chang, H.-W. Wang, G. Gan, S.-L. Lee, and T.-H. Lee	414
Surface Morphology for Hydrogen Transferred and Thinned by Oxidation SOI Layers V. Popov	424

A Nano-thick SOI Fabrication Method C.-H. Huang, J.T. Cheng, Y.-K. Hsu, C.-L. Chang, H.W. Wang, S.-L. Lee, and T.-H. Lee	431
Fabrication of Silicon-on-Diamond (SOD) Substrates T.I. Feygelson, K.D. Hobart, M. Ancona, F.J. Kub, and J.E. Butler	439
Interferometric Optical Isolator with Si Guiding Layer Operated in Unidirectional Magnetic Field H. Yokoi	450
Author Index	458
Subject Index	461